

IN THE CLAIMS:

1. (Original) A semiconductor component, **wherein** the component comprises an electroconductive element provided with at least one outlet, so that the electroconductive element is groundable via an outlet for shielding the semiconductor component against electrostatic pulses.
2. (Original) A semiconductor component according to claim 1, **wherein** in structure, the electroconductive element is a planar sheet.
3. (Original) A semiconductor component according to claim 1, **wherein** the electroconductive element is a thin loop structure.
4. (Original) A semiconductor component according to claim 1, **wherein** the electroconductive element forms a permanent, integrated part of the semiconductor component.
5. (Original) A semiconductor component according to claim 4, **wherein** the electroconductive element is placed underneath the cover element of the semiconductor component, inside said cover element.
6. (Original) A semiconductor component according to claim 4, **wherein** the electroconductive element is placed on top of the cover element of the semiconductor component, outside said cover element.
7. (Original) A semiconductor component according to claim 1, **wherein** the electroconductive element is induced in the cover element of the semiconductor component either chemically or electrochemically.
8. (Currently Amended) A method for shielding a semiconductor component against electrostatic pulses, ~~wherein in the semiconductor component, there is integrated comprising: integrating an electroconductive element in the semiconductor component, and that for the integrated electroconductive element there is provided providing at least one outlet for the integrated electroconductive element, so that the electroconductive element is groundable through the outlet.~~
9. (Original) A method according to claim 8, **wherein** in the semiconductor component, there is integrated an electroconductive, planar element.

10. (Original) A method according to claim 8, ~~wherein~~ in the semiconductor component, there is integrated an electroconductive, loop-shaped element.
11. (Currently Amended) A method according to ~~any of the preceding claims~~claim 8, ~~wherein~~ the electroconductive element is integrated as a permanent part of the semiconductor component.
12. (Original) A method according to claim 11, ~~wherein~~ the electroconductive element is integrated underneath the cover element of the semiconductor component, inside said cover element.
13. (Original) A method according to claim 11, ~~wherein~~ the electroconductive element is integrated on top of the cover element of the semiconductor component, outside said cover element.
14. (Original) A method according to claim 8, ~~wherein~~ the electroconductive element is induced in the cover element of the semiconductor component either chemically or electrochemically.
15. (Currently Amended) An apparatus including a mounting tray and components, ~~wherein a component of the device~~components comprises a semiconductor component, in which there is integrated an electroconductive element, and where the electroconductive element is provided with at least one outlet that is grounded to ~~the~~a ground plane of the mounting tray.
16. (New) Apparatus for shielding a semiconductor component against electrostatic pulses, comprising:
 - means for integrating an electroconductive element in the semiconductor component; and
 - means for providing at least one outlet for the integrated electroconductive element, so that the electroconductive element is groundable through the outlet.
17. (New) The apparatus of claim 16, wherein in the semiconductor component, there is integrated an electroconductive, planar element.
18. (New) The apparatus of claim 16, wherein in the semiconductor component, there is integrated an electroconductive, loop-shaped element.

19. (New) The apparatus of claim 16, wherein the electroconductive element is integrated as a permanent part of the semiconductor component.
20. (New) the apparatus of claim 16, wherein the electroconductive element is integrated underneath the cover element of the semiconductor component, inside said cover element.